

## Product Overview

### CNY17F2M: 6-Pin DIP High $BV_{CEO}$ Phototransistor Output Optocoupler

For complete documentation, see the data sheet.

The CNY17XM, CNY17FXM and MOC810XM devices consist of a gallium arsenide infrared emitting diode coupled with an NPN phototransistor in a dual in-line package.

### Features

- High  $BV_{CEO}$ : 70 V Minimum (CNY17XM, CNY17FXM, MOC8106M)
- Closely Matched Current Transfer Ratio (CTR)
- Minimizes Unit-to-Unit Variation
- Current Transfer Ratio In Select Groups
- Very Low Coupled Capacitance Along With No Chip-to-Pin 6 Base Connection for Minimum Noise Susceptability (CNY17FXM, MOC8106M)
- Safety and Regulatory Approvals:
  - UL1577, 4,170 VACRMS for 1 Minute
  - DIN-EN/IEC60747-5-5, 850 V Peak Working Insulation Voltage

### Applications

- AC-DC Merchant Power Supply
- Consumer Appliances
- Industrial Motor

### Part Electrical Specifications

Product	Compliance	Status	Channels	CTR (Min) (%)	CTR (Max) (%)	CTR tested @ IF (mA)	$V_{CE(sat)}$ (Max) (V)	$BV_{CEO}$ (Min) (V)	$BV_{CB}$ (Min) (V)	$BV_{EC}$ (Min) (V)	$t_{on}$ (Max) ( $\mu$ s)	$t_{off}$ (Max) ( $\mu$ s)	$V_{ISO}$ (Min) (V)	$T_{OPR}$ (Min) ( $^{\circ}$ C)	$T_{OPR}$ (Max) ( $^{\circ}$ C)	Package Type
CNY17F2M	Pb-free	Active	1	63	125	10	0.4	70	70	7	2	3	4200	-40	100	PDIP-6
CNY17F2SM	Pb-free	Active	1	63	125	10	0.4	70	70	7	2	3	4200	-40	100	PDIP-6
CNY17F2SR2M	Pb-free	Active	1	63	125	10	0.4	70	70	7	2	3	4200	-40	100	PDIP-6
CNY17F2SR2VM	Pb-free	Active	1	63	125	10	0.4	70	70	7	2	3	4200	-40	100	PDIP-6
CNY17F2SVM	Pb-free	Active	1	63	125	10	0.4	70	70	7	2	3	4200	-40	100	PDIP-6
CNY17F2TVM	Pb-free	Active	1	63	125	10	0.4	70	70	7	2	3	4200	-40	100	PDIP-6
CNY17F2VM	Pb-free	Active	1	63	125	10	0.4	70	70	7	2	3	4200	-40	100	PDIP-6

For more information please contact your local sales support at [www.onsemi.com](http://www.onsemi.com).

Created on: 9/15/2019